

DualCool™ N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16322Q5C

FEATURES

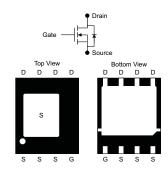
- DualCool™ Package SON 5×6mm
- Optimized for Two Sided Cooling
- Optimized for 5V Gate Drive
- Ultralow Q_q and Q_{qd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant and Halogen Free

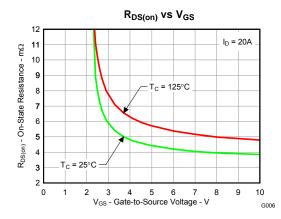
APPLICATIONS

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous or Control FET Applications

DESCRIPTION

The NexFET[™] power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25		٧
Q_g	Gate Charge Total (4.5V)	6.8		nC
Q_{gd}	Gate Charge Gate to Drain	1.3		nC
		$V_{GS} = 3V$	5.4	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	4.6	mΩ
		V _{GS} = 8V 3.9		mΩ
V _{GS(th)}	Threshold Voltage	1.1		V

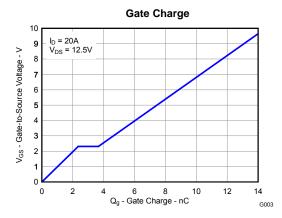
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16322Q5C	SON 5x6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -8	٧
	Continuous Drain Current, T _C = 25°C	97	Α
I _D	Continuous Drain Current ⁽¹⁾	21	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	136	Α
P_D	Power Dissipation ⁽¹⁾	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 50A$, $L = 0.1mH$, $R_G = 25\Omega$	125	mJ

- (1) $R_{\theta JA} = 39$ °C/W on 1-inch² Cu, (2-oz.) on a 0.06" thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Static C	haracteristics			,	
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_{DS} = 250 \mu A$	25		V
I _{DSS}	Drain to Source Leakage	V _{GS} = 0V, V _{DS} = 20V		1	μΑ
I _{GSS}	Gate to Source Leakage	$V_{DS} = 0V, V_{GS} = +10/-8V$		100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.1	1.4	V
		$V_{GS} = 3V$, $I_{DS} = 20A$	5.4	7.2	$m\Omega$
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$, $I_{DS} = 20A$	4.6	5.8	$m\Omega$
		$V_{GS} = 8V, I_{DS} = 20A$	3.9	5	mΩ
9 _{fs}	Transconductance	$V_{DS} = 15V, I_{DS} = 20A$	106		S
Dynamic	Characteristics	·			
C _{iss}	Input Capacitance		1050	1365	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ $f = 1MHz$	740	950	pF
C _{rss}	Reverse Transfer Capacitance	1 = 1.W.12	55	70	pF
R_G	Series Gate Resistance		1.1	2.2	Ω
Qg	Gate Charge Total (4.5V)		6.8	9.7	nC
Q _{gd}	Gate Charge – Gate to Drain	$V_{DS} = 12.5V$,	1.3		nC
Q _{gs}	Gate Charge – Gate to Source	I _{DS} = 20A	2.4		nC
Q _{g(th)}	Gate Charge at Vth		1.3		nC
Q _{oss}	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$	17		nC
t _{d(on)}	Turn On Delay Time		6.1		ns
t _r	Rise Time	V _{DS} = 12.5V, V _{GS} = 4.5V,	10.7		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 20A, R_G = 2\Omega$	12.3		ns
t _f	Fall Time		3.7		ns
Diode C	haracteristics	·			
V _{SD}	Diode Forward Voltage	$I_{DS} = 20A, V_{GS} = 0V$	0.8	1	V
Q _{rr}	Reverse Recovery Charge	V 43V I 30A 4:/4+ 300A / -	19		nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13V$, $I_F = 20A$, $di/dt = 300A/\mu s$	21		ns

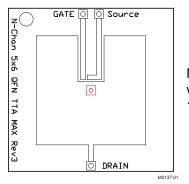
THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

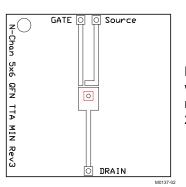
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (Top Source) ⁽¹⁾			3.5	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case (Bottom drain) ⁽¹⁾			2.4	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			50	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² 2-oz. Cu pad on a 1.5 x 1.5-inch 0.06-inch thick FR4 board. $R_{\theta JC}$ is specified by design, whereas $R_{\theta CA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² of 2-oz. Cu.





Max $R_{\theta,JA} = 50$ °C/W when mounted on 1 inch² of 2-oz. Cu.



Max $R_{\theta JA} = 123^{\circ}C/W$ when mounted on minimum pad area of 2-oz.Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

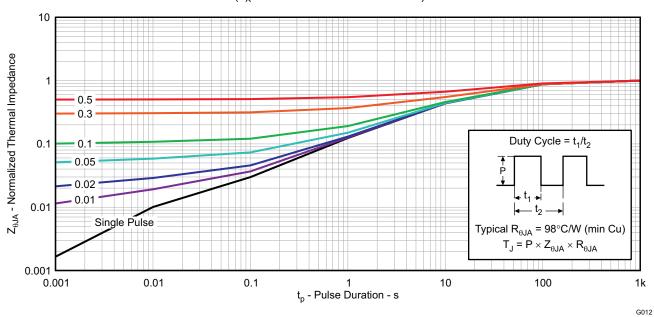


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

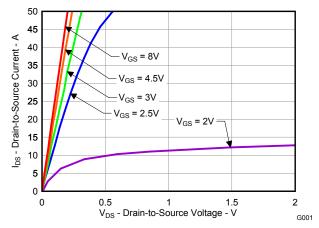


Figure 2. Saturation Characteristics

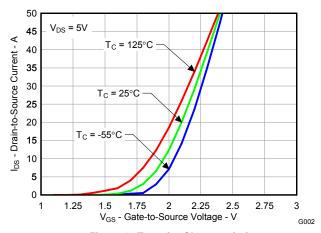


Figure 3. Transfer Characteristics

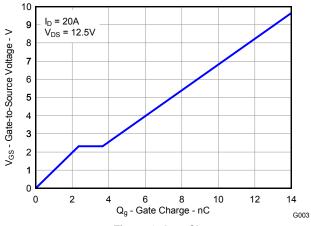


Figure 4. Gate Charge

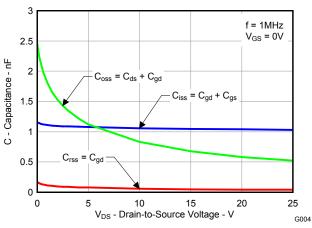


Figure 5. Capacitance

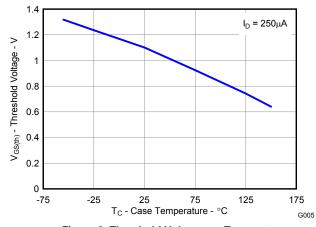


Figure 6. Threshold Voltage vs. Temperature

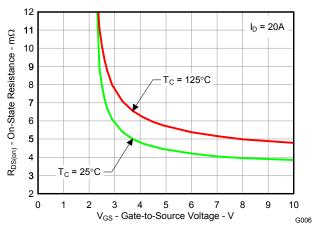


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

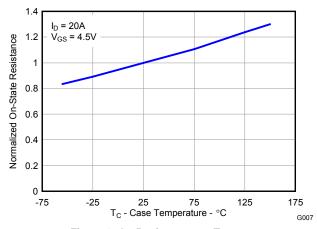


Figure 8. On Resistance vs. Temperature

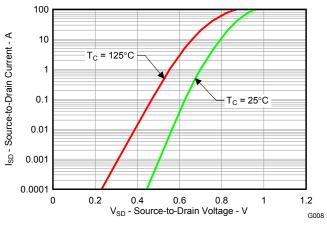


Figure 9. Typical Diode Forward Voltage

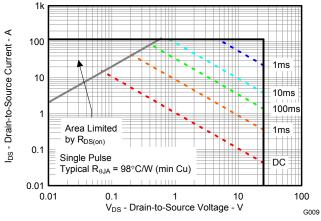


Figure 10. Maximum Safe Operating Area

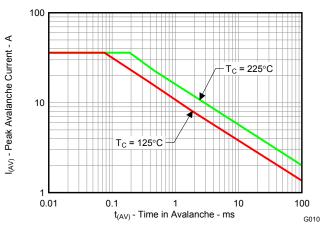


Figure 11. Single Pulse Unclamped Inductive Switching

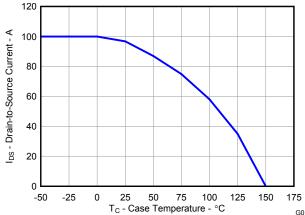
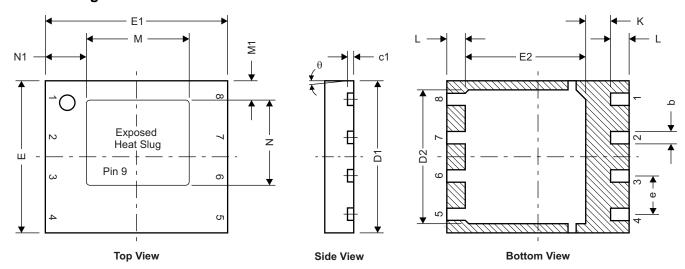


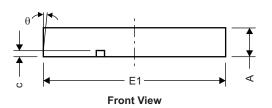
Figure 12. Maximum Drain Current vs. Temperature



MECHANICAL DATA

Q5C Package Dimensions





DualCool™Pinout			
Pin#	Label		
1, 2, 3, 9	Source		
4	Gate		
5, 6, 7, 8	Drain		

M0162-01

DIM	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
Е	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
е	1.27 TYP		0.0	050
L	0.510	0.710	0.020	0.028
θ	_	_	_	_
K	0.760	-	0.030	_
М	3.260	3.460	0.128	0.136
M1	0.520	0.720	0.020	0.028
N	2.720	2.920	0.107	0.115
N1	1.227	1.427	0.048	0.056

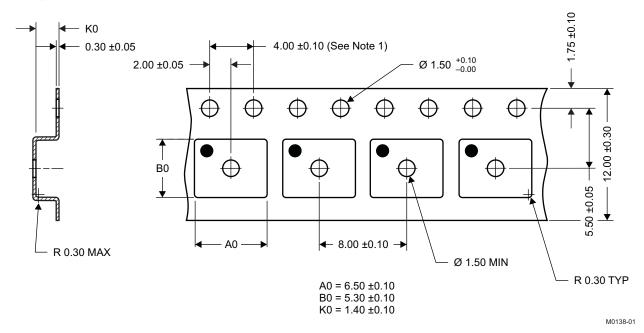


Recomme	nded PCB Pa	attern
F6 — C3 — C3 — C4 — C4 — C4 — C4 — C4 — C4	nded PCB Pa	F7 F7 F8 F8
ш.		M0139-01

DIM	MILLIMETERS		INCHES	
DIIVI	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5C Tape and Reel Information



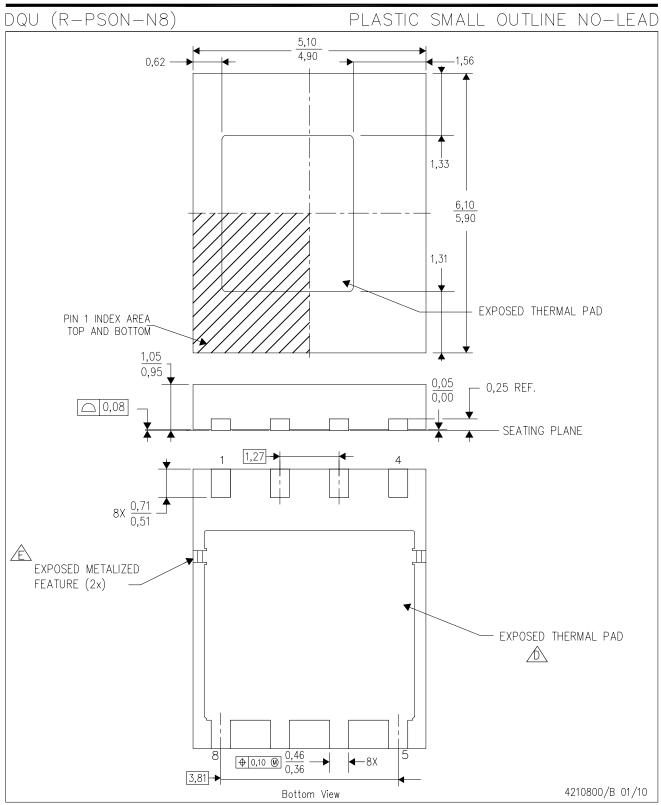
Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible



REVISION HISTORY

Changes from Original (December 2009) to Revision A	Page
Changed the labels on the Bottom View pinout image	1
Changed the Mechanical Data dimensions table. Added dimensions for M, M1, N and N1	6
Changes from Revision A (April 2010) to Revision B	Page
 Changed R_{DS(on)} - V_{GS} = 3V in the Electrical Characteristics table From: 7 To: 7.2 in the max column 	2
Deleted the Package Marking Information section	7



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. Dual Cool No-Lead (SON) package configuration.
- The package thermal pad must be soldered to the board for thermal and mechanical performance.
- $ilde{\mathbb{A}}$ Metalized features are supplier options and may not be on the package.

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